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Konstantin V. Rudenko
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Contents

| | |
|-----|-----------------------------|
| xi | <i>Authors</i> |
| xv | <i>Conference Committee</i> |
| xxi | <i>Introduction</i> |

PHYSICS OF MICRO- AND NANODEVICES

| | |
|----------|---|
| 11022 02 | Barrier-injection transit-time diodes and transistors for terahertz generation and detection (Invited Paper) [11022-106] |
| 11022 03 | Plasmonic terahertz emitters with high-aspect ratio metal gratings [11022-18] |
| 11022 04 | Silver-based double metal waveguide for terahertz quantum cascade laser [11022-35] |
| 11022 05 | Tunnel undoped multiple-gate field-effect transistor with Schottky contacts [11022-107] |
| 11022 06 | Development of a molecular single-electron transistor with a single-atom charge center [11022-77] |
| 11022 07 | Charge effects in dielectric films of MIS structures being under high-field injection of electrons at ionizing radiation [11022-56] |
| 11022 08 | Formation of surface states in MOS devices by space radiation protons [11022-79] |
| 11022 09 | Nanoscale planar ring-shaped matrix field emitters based on multilayer graphene/SiC [11022-90] |
| 11022 0A | Experimental study of a broadband vacuum photosensor with the tunnel emission from a metal nanoscale blade [11022-32] |
| 11022 0B | Static and dynamic spin-torque-diode sensitivity induced by the thermoelectric charge and spin currents in magnetic tunnel junctions [11022-114] |
| 11022 0C | Scalability analysis of magnetic-nano-junction-based STT-MRAM towards sub-20-nm technology nodes [11022-102] |
| 11022 0D | Investigations of the resistive switching of the TiN-TiO₂-SiO₂-W memristors in the oxygen atmosphere with varying pressure [11022-5] |
| 11022 0E | Nanoscale profiling and memristor effect of ZnO thin films for RRAM and neuromorphic devices application [11022-74] |

DEVICE MODELING AND SIMULATION

- 11022 0F **Simulation of graphene field-effect transistors and resonant tunneling diodes based on carbon nanomaterials** [11022-10]
- 11022 0G **Modeling of the submicron MOSFETs characteristics for UTSi technology** [11022-65]
- 11022 0H **A linear “extrinsic” compact model for short-channel MOSFET drain current asymptotic dependence on drain bias in saturation regime** [11022-46]
- 11022 0I **Compact modeling of electrical characteristics of p-MNOS based RADFETs** [11022-29]
- 11022 0J **A novel approach to model high-speed microelectronic switch on the basis of hydrodynamic approximation** [11022-30]
- 11022 0K **Quasi-hydrodynamic numerical model of high-speed on-chip photodetectors for optical interconnections** [11022-47]
- 11022 0L **Efficiency of terahertz harmonic generation in GaAs quantum wire structure: a Monte Carlo simulation** [11022-21]
- 11022 0M **Arrays of several Josephson junctions connected to oscillatory circuit** [11022-23]
- 11022 0N **Simulation of single-electron transistor based on the molecule with single-atom charge center** [11022-45]
- 11022 0O **TCAD-based performance analysis of nanoscale vacuum field-emission transistors at advanced technology nodes** [11022-104]

MEMS DEVICES AND SENSORS

- 11022 0P **A low actuation voltage MEMS switch with protection against stiction** [11022-111]
- 11022 0Q **Research of the microelectromechanical switch with different materials of metal membrane** [11022-20]
- 11022 0R **Finite-element predictive 3D modelling and optimization of membrane-based thermoresistive MEMS accelerometers** [11022-110]
- 11022 0S **ANSYS simulation of the microaccelerometer sensor** [11022-36]
- 11022 0T **Automated approach to the analysis of geometric parameters of MEMS elements** [11022-57]
- 11022 0U **Research and analysis of heat exchange processes of a micromechanical mirror based on a thermal microactuator** [11022-6]

- 11022 0V **Silicon nanobridge as a high quality mechanical resonator** [11022-13]
- 11022 0W **Determination of vibration axes of the micromachined ring resonator for the modal tuning purposes** [11022-14]
- 11022 0X **Improving the selectivity of carbon nanotube-based gas sensors via UV irradiation** [11022-91]
- 11022 0Y **Hybrid acousto-nano-biosensor** [11022-39]
- 11022 0Z **Thyroglobulin detection by biosensor based on two independent Si NW FETs** [11022-97]
- 11022 10 **High-sensitive ultra-low frequency hydrophone** [11022-60]
- 11022 11 **Influence of the electromigration on the characteristics of electrochemical microsystems** [11022-54]

MICRO- AND NANO-ELECTRIC MATERIALS AND FILMS

- 11022 12 **Silicon oxides and silicon nitrides: structure, properties and applications in memristors** [11022-33]
- 11022 13 **Swift heavy ion stimulated formation of the Si quantum dots in Si/SiO₂ multilayer heterostructures** [11022-71]
- 11022 14 **Luminescent properties of GeO_x thin films and GeO/SiO₂ heterostructures modified with swift heavy ions** [11022-28]
- 11022 15 **The manifestation of rising of the impurity density of states after the field stress in increasing of the effective electron mobility in the inversion channel at the silicon-oxide contact** [11022-44]
- 11022 16 **Features of the field damage of ultra-thin insulating layers of the silicon oxide** [11022-43]
- 11022 17 **Fabrication technology of sol-gel Al₂O₃ films for organic field-effect transistors** [11022-69]
- 11022 18 **Influence of power and pulsed regime of low frequency discharge on clusters incorporation in dielectric films for ReRAM application** [11022-37]
- 11022 19 **Structural and morphological properties of Ga(Al)N grown by MBE on 3C-SiC/Si (111) templates with off-axis and on-axis substrate orientation** [11022-50]
- 11022 1A **Laser reduction of graphene oxide thin films for nanoelectronic application** [11022-41]
- 11022 1B **Effects of vacuum-plasma etching on the electrical properties of thin ferroelectric PZT films** [11022-8]
- 11022 1C **Electric-field-induced domain switching and pinning state in lead-free ferroelectric BST 80/20 film** [11022-42]

- 11022 1D **Formation features and electrophysical properties of ferroelectric films ZnO study** [11022-53]
- 11022 1E **Influence of annealing on nanocrystalline LiNbO₃ films properties** [11022-73]
- 11022 1F **Electronic and optical properties of MoS₂ thin films deposited by magnetron sputtering studying** [11022-1]
- 11022 1G **Nanocrystalline diamond films heavily doped by boron: structure, optical and electrical properties** [11022-25]
- 11022 1H **Concept of glass formation in chalcogenide systems and the possibility of predicting new compounds for micro- and nanoelectronics** [11022-31]
- 11022 1I **The opportunities of Rutherford backscattering spectroscopy for analysis of multilayer nanometer thin film structures** [11022-66]
- 11022 1J **Effect of mechanical deformations on absorption spectrum of metallic films of nanometer thickness** [11022-51]
- 11022 1K **Different magneto-optical properties of metallized nanostructured arrays on silicon surface** [11022-4]
- 11022 1L **Energetics of domain wall in magnetic nanowire** [11022-19]

MICRO- AND NANOELECTRONIC TECHNOLOGIES I

- 11022 1M **Maskless nanolithography on the basis of microfocus x-ray tubes: conversion of electron energy into the BeK α line (Invited Paper)** [11022-67]
- 11022 1N **Cellular automata method for directed self-assembly modeling** [11022-103]
- 11022 1O **Simulation of dry e-beam etching of resist and experimental evidence** [11022-96]
- 11022 1P **Fabrication of electrodes for a logic element based on a disordered dopant atoms network** [11022-105]
- 11022 1Q **Formation of nanosized elements by ion beam lithography for multiple fin field effect transistor prototyping** [11022-68]
- 11022 1R **Mask formation on GaAs substrate by focused ion beams of Ga⁺ for plasma chemical etching** [11022-75]
- 11022 1S **Methods and means of experimental investigation of gas-phase deposition of material layers in MEMS processes** [11022-7]
- 11022 1T **Synergistic effects of deformation and solid state reactions in Si with buried glass layer initiated by annealing in non-isothermal reactor** [11022-22]

- 11022 1U **Induced bistability into quartz glass by silicon wafer heat treatment in lamp-based reactor** [11022-48]
- 11022 1V **Localization of a thermo-optical traveling wave at an optical inhomogeneity in a silicon wafer under lamp-based heating** [11022-24]
- 11022 1W **Investigation of technological operations for manufacturing 3D micro-assemblies with embedded elements** [11022-40]

MICRO- AND NANOELECTRONIC TECHNOLOGIES II

- 11022 1X **Deep silicon plasma etching: selection of processes for different applications (Invited Paper)** [11022-109]
- 11022 1Y **Sidewall defects in deep cryogenic Si etching in SF₆/O₂ plasma: a numerical simulation** [11022-83]
- 11022 1Z **Features of silicon deep plasma etching process at 3D-TSV structures producing** [11022-52]
- 11022 20 **Effect of the sublayer material on the formation of electrical contact and the growth rate of carbon nanotubes in a low-temperature plasma using the example of Ni/Ti/Si and Fe/W/Si structures** [11022-76]
- 11022 21 **Formation of metallic nanowire and nanonet structures on the surface of SiO₂ by combine plasma etching processes** [11022-16]
- 11022 22 **Fabrication and properties of SOI-based planar silicon nanowire arrays** [11022-95]
- 11022 23 **Effect of Ar ion-plasma treatment on residual stress in thin Cr films** [11022-26]
- 11022 24 **Plasma deposition of carbon-silicon nanocomposite for microelectromechanical applications** [11022-61]
- 11022 25 **Cyclic discrete etching of Silicon oxide in deposition-sputtering cycles: towards to ALE** [11022-99]
- 11022 26 **Study of synergy phenomena for atomic layer etching of aluminum and hafnium oxides** [11022-100]
- 11022 27 **Optical emission spectra of BF₃/Ar-plasma: detection of the boron 563.3-nm spectral line and identification of BF band spectra** [11022-72]

QUANTUM INFORMATICS I

- 11022 28 **Broadband impedance matching in white cavity (Invited Paper)** [11022-94]
- 11022 29 **Robust random number generator based on field effect transistor** [11022-89]

- 11022 2A **Quantum computer based on triangular atom-photon molecule** [11022-92]
- 11022 2B **Multi-qubit controlled NOT gates for artificial intelligence natural languages processing** [11022-93]
- 11022 2C **Homogeneous atomic ensembles and single-mode field: review of simulation results (Invited Paper)** [11022-34]
- 11022 2D **Quantum lock on dark states (Invited Paper)** [11022-116]
- 11022 2E **Multiple quantum coherence transfer and quantum correlations in NMR experiments in solids** [11022-3]
- 11022 2F **Quantum entanglement in trimer clusters** [11022-2]
- 11022 2G **Quantum entanglement in spin chains with the XY Hamiltonian at the quantum state transfer** [11022-27]
- 11022 2H **Quantum information processing with macroscopic two-component Bose-Einstein condensates** [11022-88]
- 11022 2I **Jumps of optimal measurement angle and fractures on the curves of quantum correlation functions** [11022-17]
- 11022 2J **Hitting time for quantum walks of identical particles** [11022-55]

QUANTUM INFORMATICS II

- 11022 2K **Multiphoton subtracted thermal states: description, preparation, measurement and utilization** [11022-64]
- 11022 2L **Theoretical and experimental study of multi-mode thermal states with subtraction of a random number of photons** [11022-49]
- 11022 2M **Quantum tomography based on principles of completeness, adequacy and fidelity** [11022-86]
- 11022 2N **High-fidelity quantum tomography with imperfect measurements** [11022-82]
- 11022 2O **The concept of weak measurements and the super-efficiency of quantum tomography** [11022-63]
- 11022 2P **On the fidelity of quantum gates under T1 and T2 relaxation** [11022-78]
- 11022 2Q **Quantum approach to the dynamical systems modeling** [11022-84]
- 11022 2R **Representation of Boolean functions in terms of quantum computation** [11022-62]

- 11022 2S **Machine learning methods in quantum computing theory** [11022-85]
- 11022 2T **Two-way quantum and classical machines with small memory for online minimization problems** [11022-98]
- 11022 2U **Molecule ground state energy estimation via continuous-time quantum walks** [11022-101]
- 11022 2V **Sequences of selective rotation operators to engineer interactions for quantum annealing on three qutrits** [11022-15]
- 11022 2W **Fast quantum randomness generation from vacuum fluctuation induced phase diffusion between pulses of laser diode** [11022-87]

Authors

Numbers in the index correspond to the last two digits of the seven-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first five digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Aban'shin, Nikolay P., 0A
Abdullaev, D. A., 1B
Ablayev, F. M., 29, 2A, 2B
Abramov, Igor I., 0F
Adonin, A. S., 0G
Afanasyev, Mikhail S., 1C
Afonenko, A., 04
Ageev, Oleg A., 09, 0E, 1E, 1R, 20, 24
Akchurin, Garif G., 0A
Alodjants, Aleksandr P., 2J
Al-Saman, A., 0J
Amirov, I. I., 21, 23
Anchutin, S., 0S
Andreev, Dmitrii V., 07, 08
Andreev, V. G., 1J
Andreev, Vladimir V., 07
Andrianov, S. N., 29, 2A, 2B
Andrianova, N. S., 2B
Anisimkin, Vladimir V., 0Y
Avdeev, Sergey P., 17
Averkin, S. N., 1X
Avetisyan, Yuri A., 0A
Avilov, Vadim I., 0E
Avosopiants, G. V., 2K, 2L
Babushkin, A., 23
Bachurin, V., 1I
Bantysh, B. I., 2K, 2M, 2N, 2O, 2S
Belikov, A. I., 1F
Belin, A. M., 0R
Beloglazkina, E., 06
Belov, A. N., 1D
Belyaev, A. Y., 10
Berdnikov, A. E., 18
Bobrinetskii, I., 0X
Bochkin, G. A., 2E
Bogachev, V. V., 1A
Bogdanov, Yu. I., 2K, 2L, 2M, 2N, 2O, 2Q, 2R, 2S
Bogdanova, N. A., 2L, 2M, 2O, 2Q, 2R
Borzdov, Andrei V., 0L
Borzdov, Vladimir M., 0L
Bozhev, I. V., 0V, 0Z
Bruk, M., 1O
Byrnes, Tim, 2H
Cherkova, S. G., 13, 14, 1G
Chernyavskiy, Andrey Yu., 2P
Chkhalo, N. I., 1M
Chubunov, P., 0I
Chucheva, Galina V., 15, 16, 1C
Churilov, A., 1I
Clemente, Iosif E., 1E
Dagesyan, Sarkis A., 06, 0Y, 1P
Danelyan, E. E., 1A
Demin, Gleb D., 0B, 0C, 0O, 0R, 1M
Denisenko, Yuri I., 1T
Dorofeev, A. A., 0V
Dubinov, A., 04
Dudkin, P. V., 10, 11
Dukhan, Denis D., 0E
Dyuzhev, N. A., 0O, 0R, 1M
Ermakov, Roman, 2W
Evsikov, I. D., 0O
Evstafyev, S., 0U, 1S
Ezhova, Olga A., 0Q
Fastovets, D. V., 2M, 2N, 2Q, 2R, 2S
Fedichkin, Leonid E., 2J, 2U
Fedorova, A. V., 2E
Fedotov, S. D., 19, 1Q
Fel'dman, E. B., 2E, 2F
Gaydamachenko, V. R., 06, 1P
Gerasimov, K. I., 28
Gismatulin, A. A., 13
Glinskiy, I. A., 03
Goldman, Evgeny I., 15, 16
Golishnikov, A. A., 1Z
Gorlachev, E. S., 0D, 2I
Gornev, E. S., 1I, 1N
Granato, E., 1L
Gritsenko, V. A., 12
Gulyaev, Yuriy V., 16
Gusev, Evgeny Yu., 09, 17, 24
Gushin, O., 1N
Iñiguez, B., 0H
Isachenko, A., 0T
Izrailev, N., 0T
Izyumov, M. O., 2I
Jityaev, I. L., 09
Jityaeva, Julia Y., 24
Kafanov, S. G., 0V
Kalachev, A. A., 2B
Kalinin, V. N., 1F
Kalugin, V., 0S
Kamaev, G. N., 12, 13
Kashin, Vadim V., 0Y
Katamadze, K. G., 2K, 2L
Kazachkov, A., 0T
Khabibullin, R. A., 03, 04
Khadiev, Kamil, 2T
Khadieva, Aliya, 2T

Khartov, S., 0X
 Kiselev, Dmitry A., 1C
 Klimin, Viktor S., 0E, 1E, 1R, 20
 Kochurina, E., 0S
 Kokhanovsky, S. V., 10
 Kolesov, Vladimir V., 0Y
 Kolomejtseva, Natali V., 0F
 Kolotinskiy, Nikolay V., 0M
 Komarov, I. A., 1A
 Konoplev, B. G., 0K
 Kornev, Victor K., 0M
 Korobova, Natalia E., 1H
 Kostyukov, D. A., 1Z
 Kots, Ivan N., 1R
 Krishtop, T. V., 10, 11
 Krishtop, V. G., 10, 11
 Krivospitsky, A., 05
 Kruchinin, S., 1W
 Kruchinin, V. N., 12
 Krupenin, V. A., 0V, 0Z
 Kshensky, O., 0H
 Kudrya, V., 27
 Kudryavtsev, S. E., 0D
 Kulagin, A. V., 2C
 Kulik, S. P., 2K, 2L
 Kumar, V., 1G
 Kupriyanov, Alexander N., 0P
 Kurbat, D., 1Y
 Kurenja, Alexey L., 1V
 Kurochkin, Vladimir, 2W
 Kurochkin, Yuriy, 2W
 Kuzmenko, V. O., 11
 Kuzmenko, V., 25, 26
 Kuznetsov, Yu. A., 2O
 Kuznetsova, E. I., 2F, 2G
 Kuznetsova, Iren E., 0Y
 Labunov, Vladimir A., 0F, 0L
 Ladunov, V. Y., 2C
 Lagodenko, N. K., 1A
 Lapshin, R. V., 0R
 Lavrukhin, D. V., 03
 Lazarev, I. D., 2G
 Levin, D. D., 1A
 Lisitsyn, Sergey A., 24
 Litavrin, M., 1N
 Loginov, Alexander P., 0A
 Lopatin, A. Ya., 1M
 Losev, Anton, 2W
 Lukichev, V. F., 02, 05, 1X, 1Y, 2M, 2Q, 2R, 2S
 Lysenko, Igor E., 0Q
 Makhaboroda, M. A., 0O, 1M
 Martynov, A. I., 1Q
 Maslovsky, Vladimir M., 07, 08
 Matyushkin, I., 1N
 Mazaletsky, L. A., 21
 Melesov, N., 11
 Melnikov, Alexander E., 0Y
 Melnikov, Alexey A., 2J
 Meshchaninov, Fedor P., 2U
 Miakonkikh, Andrey V., 02, 05, 1E, 1X, 1Y, 22, 25,
 26
 Minaev, Viktor S., 1H
 Moiseev, E. S., 28
 Moiseev, S. A., 28, 2A
 Mordvintsev, V. M., 0D
 Morozov, O. V., 0W
 Morozova, E., 06
 Mortet, V., 1G
 Mrozovskaya, E., 0I
 Nabiev, Asaf, 15
 Naryshkina, Valentina G., 15
 Nekrasov, N., 0X
 Nevolin, V. K., 0X, 19, 1Q
 Novikov, D. V., 0R
 Orlov, M. A., 1A
 Otsuji, T., 03
 Ovcharov, Vladimir V., 1U, 1V
 Ovodov, A. I., 0R
 Ozhigov, Y. I., 2C, 2D
 Paporkov, Vladimir A., 1K
 Parshin, E., 1I
 Parshintsev, A. A., 0N
 Pashkin, Yu. A., 0V
 Pavlovskiy, V., 04
 Perevalov, A. A., 1D
 Pestov, A. E., 1M
 Petrosyants, K. O., 0G
 Pichkovskiy, I. S., 2V
 Pisarenko, I. V., 0K
 Polyakova, Victoria V., 1R
 Ponomarev, D. S., 03, 04
 Popkov, Anatoly F., 0B, 0C
 Popov, A. A., 18
 Popov, A. V., 0C
 Popov, D. A., 0G
 Poyarkov, V., 0H
 Presnov, D. E., 0V, 0Z, 1P
 Presnova, G. V., 0Z
 Prigara, Valeriya P., 1U, 1V
 Prokaznikov, Alexander V., 1K
 Putrya, M. G., 1Z
 Pyrkov, Alexey N., 2H
 Remes, Z., 1G
 Rezvan, Alexey A., 0E, 1R, 20
 Rinnert, H., 14
 Rod, I., 0T
 Rogozhin, Alexander E., 02, 1O, 22
 Romanov, V. S., 29
 Romanova, Irina A., 0F
 Rubtsova, M. Yu., 0Z
 Rudakov, Valery I., 1V
 Rudenko, Konstantin V., 02, 05, 1E, 1X, 22, 25, 26
 Rudenko, M., 02, 1Y
 Rudy, A., 1I
 Ryndin, E. A., 0J, 0K
 Ryzhenkova, S. Yu., 1P
 Ryzhii, M., 03
 Sabooni, M., 28
 Sachkov, V. A., 1G

Safonov, D., 04
 Salashchenko, N. N., 1M
 Saletsky, A. M., 1J
 Samoylikov, V., 0U, 1S
 Sapkov, I. V., 1P
 Scherbin, S. N., 1A
 Selyukov, R., 23
 Semin, Yu., 05
 Semochkin, A. I., 1F
 Seregin, D. S., 1B
 Shamiryan, D., 0T
 Sharoglazova, Violetta, 2W
 Shchavruk, N., 04
 Shcherbakova, Irina Y., 0F
 Shevyakov, V. I., 1D, 1Z
 Shkarlat, R., 0H
 Shorokhov, V. V., 0N, 0Z
 Shur, M., 03, 0H
 Sidorov, F., 1O
 Silakov, G. O., 1A
 Skovoroda, N. A., 2C
 Skuratov, V. A., 13, 14
 Smelova, E. M., 1J
 Smirnov, Andrey V., 0Y
 Smirnov, Vladimir A., 0E
 Soldatov, Eugeniï S., 06, 0N, 0Y
 Soloviev, A. A., 29
 Statsenko, V. N., 19
 Stepanov, A. S., 1P
 Stoffel, M., 14
 Stolyarov, Alexander A., 07
 Struchkov, N. S., 1A
 Stuchlik, J., 1G
 Stuchliková, T. H., 1G
 Svetlichnyi, A. M., 09
 Tashchilina, A., 28
 Tatarintsev, Andrey A., 22
 Taylor, A., 1G
 Timoshenkov, Sergey P., 0S, 1H, 1W
 Tkachenko, Alexey V., 0Q
 Tominov, Roman V., 0E, 1E
 Trifonov, A. S., 0V, 0Z
 Trushin, O. S., 1I, 1L
 Tsarik, K. A., 19, 1Q
 Tsiniakin, I. I., 0Z
 Tsysar, K. M., 1J
 Turin, V., 0H
 Ulyashova, M. M., 0Z
 Ushakov, D., 04
 Uvarov, Iliia V., 0P, 0W
 Vahrushev, D. V., 29
 Vakulov, Zakhar E., 1E
 Varzarev, Yuriy N., 1E
 Vasil'evskii, I., 04
 Vasiliev, A. V., 2A, 2B
 Vdovin, V. A., 1J
 Vergnat, M., 14
 Victorova, N. B., 2C
 Volkov, Artem N., 08
 Volkov, O., 04
 Volodin, V. A., 12, 13, 14, 1G
 Vorotilov, K. A., 1B
 V'yurkov, Vladimir V., 02, 05, 0L
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 Yakunin, Alexander N., 0A
 Ying, S. C., 1L
 Yurischev, M. A., 2I
 Yuvchenko, Sergey A., 0A
 Zamburg, Evgeny G., 0E
 Zavodilenko, Vladimir, 2W
 Zaytsev, K. I., 03
 Zebrev, G., 0H, 0I
 Zelensky, V. S., 1J
 Zenchuk, A. I., 2E
 Zhabin, S. N., 1I
 Zharik, G. A., 1P
 Zhevnenko, D. A., 10, 1I
 Zhikharev, E., 1O
 Ziatdinov, M. T., 29
 Zimin, P., 0I
 Zimnyakov, Dmitry A., 0A
 Zin Phyo, Kyaw, 1F
 Zlobin, A. S., 10
 Zobov, V. E., 2V
 Zotov, A. O., 1D
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Plenary Session II: Quantum Informatics I

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Plenary Session III: THz Photonics

Vladimir V. Vyurkov, Valiev Institute of Physics and Technology of Russian
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1 2D Materials for Nanodevices

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- 4 Advanced Nanoelectronic Technologies
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- 5 Modeling and Simulation of FETs
Vladimir V. Vyurkov, Valiev Institute of Physics and Technology of Russian
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- 6 Quantum Informatics III
Yurii I. Ozhigov, Lomonosov Moscow State University (Russian Federation)
- 7 Nanoscale Lithography
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- 8 Spintronics Devices
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- 9 Quantum Informatics IV
Aleksey A. Kalachev, Zavoisky Physical-Technical Institute of Russian
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- 10 Beyond CMOS
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- 11 Solid State THz Electronics
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- 12 Quantum Informatics V
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- 13 Superconducting Devices
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- 14 MEMS Devices
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- 15 Quantum Informatics VI
Eduard B. Fel'dman, Institute of Problems of Chemical Physics of Russian Academy of Sciences (Russian Federation)
- 16 Plasma Processing
Ildar I. Amirov, Valiev Institute of Physics and Technology of Russian Academy of Sciences, Yaroslavl Branch (Russian Federation)
- 17 Metrology and Characterization I
Andrey V. Miakonkikh, Valiev Institute of Physics and Technology of Russian Academy of Sciences (Russian Federation)
- 18 Quantum Informatics VII
Sergei A. Moiseev, Kazan Quantum Center, Kazan Scientific Research Technical University (Russian Federation)
- 19 30th Anniversary of the Valiev Institute of Physics and Technology of Russian Academy of Sciences
Vladimir F. Lukichev, Valiev Institute of Physics and Technology of Russian Academy of Sciences (Russian Federation)
- 20 Metrology and Characterization II
Andrey V. Miakonkikh, Valiev Institute of Physics and Technology of Russian Academy of Sciences (Russian Federation)
- 21 Integrated Photonic Devices
Eugeny A. Ryndin, Southern Federal University (Russian Federation)

Introduction

This volume contains selected papers presented at the International Conference on Micro- and Nanoelectronics 2018 (ICMNE-2018), which was held in Zvenigirod, Moscow Region (Russian Federation), 1–5 October 2018. ICMNE is a biannual conference covering the main fields of micro- and nanoelectronic technologies and device physics. Since 1992, the Valiev Institute of Physics and Technology of the Russian Academy of Sciences (Moscow, Russian Federation) has been the permanent organizer of ICMNE. SPIE has published the proceedings for ICMNE since 2003.

The ICMNE-2018 scope contained such scientific and technological fields as physics and technologies of micro- and nanodevices; simulation and modeling; MEMS physics and technology; materials and films for micro- and nanoelectronics; metrology; and quantum informatics. ICMNE-2018 included three plenary sessions, an extended Session on Quantum Informatics, and 21 topical sessions covering the following areas of focus:

- Emerging Devices
- Solid State THz Electronics and Photonics
- Beyond CMOS
- Modeling and Simulation of FETs
- Superconducting and Spintronics Devices
- Integrated Photonic Devices
- MEMS Devices
- 2D Materials and Thin Films for Micro- and Nanodevices
- Advanced Nanoelectronic Technologies
- Nanoscale Lithography
- Plasma Processing
- Metrology and Characterization
- Quantum Informatics.

The scientific program was based on invited and contributed papers from scientists from the European and Siberian Regions of Russian Federation, Belarus, Austria, Italy, United Kingdom, United States, and Japan. The invited lectures on current achievements and challenges in contemporary microelectronics were delivered by scientists from Austria, Italy, United Kingdom, United States, Japan, and Russian Federation. The contributions to the sessions of the conference were made by academic institutions, universities, as well as industry. More than 100 contributions were discussed as oral presentations and about 100 others were presented as posters.

We hope that helpful discussions of these works at the sessions of the conference and during personal contacts between attendees will promote research activity in the microelectronic community. Additional information about ICMNE-2018 can be found at the conference website <http://www.icmne.ftian.ru>

Vladimir F. Lukichev
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